

### **EMC OPTIMIZED CAN TRANSCEIVER**

#### **FEATURES**

- Improved Replacement for the TJA1050
- High Electromagnetic Immunity (EMI)
- Very Low Electromagnetic Emissions (EME)
- Meets or Exceeds the Requirements of ISO 11898-2
- Bus-Fault Protection of –27 V to 40 V
- Dominant Time-Out Function
- Power-Up/Down Glitch-Free Bus Inputs and Outputs
  - High Input Impedance with Low V<sub>CC</sub>
  - Monotonic Outputs During Power Cycling

#### **APPLICATIONS**

- Industrial Automation
  - DeviceNet<sup>™</sup> Data Buses (Vendor ID #806)
- SAE J2284 High Speed CAN for Automotive Applications
- SAE J1939 Standard Data Bus Interface
- ISO 11783 Standard Data Bus Interface
- NMEA 2000 Standard Data Bus Interface

#### **DESCRIPTION**

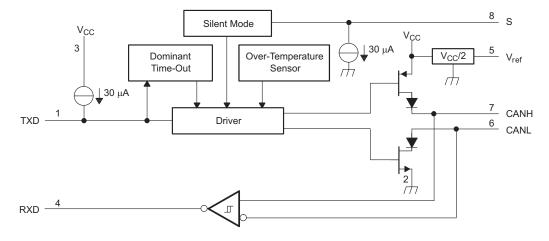
The SN65HVD1050 meets or exceeds the specifications of the ISO 11898 standard for use in applications employing a Controller Area Network (CAN). The device is also qualified for use in automotive applications in accordance with AEC-Q100.<sup>(1)</sup>

As a CAN transceiver, this device provides differential transmit capability to the bus and differential receive capability to a CAN controller at signaling rates up to 1 megabit per second (Mbps)<sup>(2)</sup>.

Designed for operation is especially harsh environments, the HVD1050 features cross-wire, over-voltage and loss of ground protection from -27 V to 40V, over-temperature shut down, a -12 V to 12 V common-mode range, and will withstand voltage transients from -200 V to 200 V according to ISO 7637.

- The device is available with Q100 qualification as the SN65HVD1050Q (PRODUCT PREVIEW).
- (2) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

#### **FUNCTION BLOCK DIAGRAM**



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **DESCRIPTION (CONTINUED)**

Pin 8 provides for two different modes of operation: high-speed or silent mode. The high-speed mode of operation is selected by connecting S (pin 8) to ground.

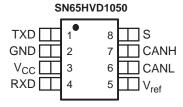
If a high logic level is applied to the S pin of the SN65HVD1050, the device enters a listen-only silent mode during which the driver is switched off while the receiver remains fully functional.

In silent mode, all bus activity is passed by the receiver output to the local protocol controller. When data transmission is required, the local protocol controller reverses this low-current silent mode by placing a logic-low on the S pin to resume full operation.

A dominant-time-out circuit in the SN65HVD1050 prevents the driver from blocking network communication with a hardware or software failure. The time-out circuit is triggered by a falling edge on TXD (pin 1). If no rising edge is seen before the time-out constant of the circuit expires, the driver is disabled. The circuit is then reset by the next rising edge on TXD.

 $V_{\text{ref}}$  (pin 5) is available as a  $V_{\text{CC}}/2$  voltage reference.

The SN65HVD1050 is characterized for operation from -40°C to 125°C.



#### ORDERING INFORMATION

PART NUMBER	PACKAGE	MARKED AS	ORDERING NUMBER
SN65HVD1050	SOIC-8	VP1050	SN65HVD1050D (rail)
3140311701030	3010-6	VP1030	SN65HVD1050DR (reel)

#### ABSOLUTE MAXIMUM RATINGS(1)

		UNIT
$V_{CC}$	Supply voltage <sup>(2)</sup>	−0.3 V to 7 V
	Voltage range at any bus terminal (CANH, CANL, V <sub>ref</sub> )	–27 V to 40 V
Io	Receiver output current	20 mA
VI	Voltage input, transient pulse (3) (CANH, CANL)	-200 V to 200 V
$V_{I}$	Voltage input range (TXD, S)	-0.5 V to 6 V
$T_{J}$	Junction temperature	−55°C to 170°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

<sup>(2)</sup> All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

<sup>(3)</sup> Tested in accordance with ISO 7637, test pulses 1, 2, 3a, 3b, 5, 6, and 7.



#### **ELECTROSTATIC DISCHARGE PROTECTION**(1)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		
IEC Contact Discharge	IEC 61000-4-2	Bus terminals vs GND	±6 kV	
Lluman Dady Madal	JEDEC Standard 22,	Bus terminals vs GND	±8 kV	
Human Body Model	Test Method A114-C.01	All pins	±4 kV	
Field-Induced-Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1.5 kV	
Machine Model	ANSI/ESDS5.2-1996		±200 V	

<sup>(1)</sup> All typical values at 25°C.

#### RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		4.75		5.25	V
V <sub>I</sub> or V <sub>IC</sub>	Voltage at any bus terminal	age at any bus terminal (separately or common mode)			12	V
V <sub>IH</sub>	High-level input voltage	TVD C	2		5.25	V
V <sub>IL</sub>	Low-level input voltage	TXD, S	0		0.8	V
$V_{ID}$	Differential input voltage		-7		7	V
	High lavel autout aumant	Driver	-70			A
IOH	High-level output current	Receiver	-2			mA
	Laurian autout aumant	Driver			70	A
I <sub>OL</sub>	Low-level output current	Receiver		2		mA
TJ	Junction temperature	See Thermal Characteristics table, 1 Mbps minimum signaling rate with $R_L=54\Omega$	-40		150	°C

#### **SUPPLY CURRENT**

over recommended operating conditions (unless otherwise noted)

	PARAM	IETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		Silent mode	S at $V_{CC}$ , $V_I = V_{CC}$		6	10	•
I <sub>CC</sub>	5-V Supply current	Dominant	$V_I = 0 \text{ V}$ , 60 $\Omega$ Load, S at 0 V		50	70	mA
		Recessive	V <sub>I</sub> = V <sub>CC</sub> , No Load, S at 0 V		6	10	

#### **DEVICE SWITCHING CHARACTERISTICS**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
t <sub>d(LOOP1)</sub>	Total loop delay, driver input to receiver output, recessive to dominant	Figure 0. S at 0V	90	190	
t <sub>d(LOOP2)</sub>	Total loop delay, driver input to receiver output, dominant to recessive	Figure 9, S at 0V	90	190	ns

#### **DRIVER ELECTRICAL CHARACTERISTICS**

over recommended operating conditiions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
\/	Pug output valtage (Deminant)	CANH	$V_I = 0 \text{ V}$ , S at 0 V, $R_L = 60 \Omega$ , See Figure 1	2.9	3.4	4.5	\/
V <sub>O(D)</sub>	Bus output voltage (Dominant)	CANL	and Figure 2	0.8		1.5	v
V <sub>O(R)</sub>	Bus output voltage (Recessive)		$V_I$ = 3 V, S at 0 V, $R_L$ = 60 $\Omega$ , See Figure 1 and Figure 2	2	2.3	3	V

(1) All typical values are at 25°C with a 5-V supply.



#### **DRIVER ELECTRICAL CHARACTERISTICS (continued)**

over recommended operating conditiions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
V	Differential output voltage (Dominant)	$V_I$ = 0 V, $R_L$ = 60 $\Omega$ , S at 0 V, See Figure 1, Figure 2, and Figure 3	1.5		3	V
V <sub>OD(D)</sub>		$V_I$ = 0 V, $R_L$ = 45 $\Omega$ , S at 0 V, See Figure 1, Figure 2, and Figure 3	1.4		3	V
M	Differential output valtage (Peccesive)	V <sub>I</sub> = 3 V, S at 0 V, See Figure 1 and Figure 2	-0.012		0.012	V
$V_{OD(R)}$	Differential output voltage (Recessive)	V <sub>I</sub> = 3 V, S at 0 V, No Load	-0.5		0.05	V
V <sub>OC(ss)</sub>	Steady state common-mode output voltage	S at 0 V Figure 0	2	2.3	3	V
$\Delta V_{OC(ss)}$	Change in steady-state common-mode output voltage	S at 0 V, Figure 8		30		mV
I <sub>IH</sub>	High-level input current, TXD input	V <sub>I</sub> at V <sub>CC</sub>	-2		2	
I <sub>IL</sub>	Low-level input current, TXD input	V <sub>I</sub> at 0 V	-50		-10	μΑ
I <sub>O(off)</sub>	Power-off TXD output current	V <sub>CC</sub> at 0 V, TXD at 5 V			1	
		V <sub>CANH</sub> = -12 V, CANL Open, See Figure 11	-105	-72		
	Chart aireuit ataady atata autaut aurrant	V <sub>CANH</sub> = 12 V, CANL Open, SeeFigure 11		0.36	1	mA
I <sub>OS(ss)</sub>	Short-circuit steady-state output current	V <sub>CANL</sub> = -12 V, CANH Open, See Figure 11	-1	-0.5		IIIA
		V <sub>CANL</sub> = 12 V, CANH Open, See Figure 11		71	105	
Co	Output capacitance	See receiver input capacitance				

#### DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output		25	65	120	
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output	S at 0 V, See Figure 4	25	45	90	
t <sub>r</sub>	Differential output signal rise time	S at 0 V, See Figure 4		25		ns
t <sub>f</sub>	Differential output signal fall time			50		
t <sub>en</sub>	Enable time from silent mode to dominant	See Figure 7			1	μs
t <sub>(dom)</sub>	Dominant time-out	↓V <sub>I</sub> , See Figure 10	300	450	700	μs

#### RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
$V_{IT+}$	Positive-going input threshold voltage	S at 0 V See Table 4		800	900	
$V_{\text{IT-}}$	Negative-going input threshold voltage	S at 0 V, See Table 1	500	650		mV
V <sub>hys</sub>	Hysteresis voltage (V <sub>IT+</sub> – V <sub>IT-</sub> )		100	125		
V <sub>OH</sub>	High-level output voltage	I <sub>O</sub> = -2 mA, See Figure 6	4	4.6		V
$V_{OL}$	Low-level output voltage	I <sub>O</sub> = 2 mA, See Figure 6		0.2	0.4	V
I <sub>I(off)</sub>	Power-off bus input current	CANH or CANL = 5 V, Other pin at 0 V, V <sub>CC</sub> at 0 V, TXD at 0 V		165	250	μΑ
I <sub>O(off)</sub>	Power-off RXD leakage current	V <sub>CC</sub> at 0 V, RXD at 5 V			20	μΑ
Cı	Input capacitance to ground, (CANH or CANL)	TXD at 3 V, V <sub>I</sub> = 0.4 sin (4E6πt) + 2.5 V		13		pF
C <sub>ID</sub>	Differential input capacitance	TXD at 3 V, $V_I = 0.4 \sin (4E6\pi t)$		5		-
R <sub>ID</sub>	Differential input resistance	TXD at 3 V, S at 0 V	30		80	kΩ
R <sub>IN</sub>	Input resistance, (CANH or CANL)	TAD at 3 v, 3 at 0 v	15	30	40	K12

All typical values are at 25°C with a 5-V supply.

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#### RECEIVER ELECTRICAL CHARACTERISTICS (continued)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
R <sub>I(m)</sub>	Input resistance matching [1 – (R <sub>IN (CANH)</sub> ) / R <sub>IN (CANL)</sub> )] x 100%	$V_{(CANH)} = V_{(CANL)}$	-3%	0%	3%	

#### RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output		60	100	130	ns
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output	S at 0 V at V Saa Figure 6	45	70	90	ns
t <sub>r</sub>	Output signal rise time	S at 0 V or V <sub>CC</sub> , See Figure 6		8		ns
t <sub>f</sub>	Output signal fall time			8		ns

#### S-PIN CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I <sub>IH</sub>	High level input current	S at 2 V	20	40	70	
I <sub>IL</sub>	Low level input current	S at 0.8 V	5	20	30	μΑ

#### **VREF-PIN CHARACTERISTICS**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vo	Reference output voltage	–50 μA < I <sub>O</sub> < 50 μA	$0.4~V_{CC}$	0.5 V <sub>CC</sub>	0.6 V <sub>CC</sub>	V

#### THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
0	Lunation to Air	Low-K thermal resistance <sup>(1)</sup>	211		
$\theta_{JA}$	Junction-to-Air	High-K thermal resistance	131		
$\theta_{JB}$	Junction-to-Board Thermal Resistance	53			°C/W
$\theta_{JC}$	Junction-to-Case Thermal Resistance		79		
P <sub>D</sub> Average power dissipation	$V_{CC}$ = 5.0 V, $T_j$ = 27°C, $R_L$ = 60 $\Omega$ , S at 0 V, Input to TXD a 500 kHz, 50% duty cycle square wave. CL at RXD = 15 pF	112		mW	
	Average power dissipation	$V_{CC}$ = 5.5 V, $T_{j}$ = 130°C, $R_{L}$ = 45 $\Omega,$ S at 0 V, Input to TXD a 500 kHz, 50% duty cycle square wave. CL at RXD = 15 pF		170	
T <sub>J_shutdown</sub>	Junction temperature, thermal shutdown (2)		190		°C

<sup>(1)</sup> Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface-mount packages.

<sup>(2)</sup> Extended operation in thermal shutdown may affect device reliability, see APPLICATIONS INFORMATION.



#### **FUNCTION TABLES**

#### **DRIVER**

INP	UTS	OUTP	BUS STATE	
TXD <sup>(1)</sup>	S <sup>(1)</sup>	CANH <sup>(1)</sup>	CANL <sup>(1)</sup>	
L	L or Open	Н	L	DOMINANT
Н	X	Z	Z	RECESSIVE
Open	Х	Z	Z	RECESSIVE
Х	Н	Z	Z	RECESSIVE

(1) H = high level; L = low level; X = irrelevant; ? = indeterminate; Z = high impedance

#### **RECEIVER**

DIFFERENTIAL INPUTS V <sub>ID</sub> = V(CANH) - V(CANL)	OUTPUT RXD <sup>(1)</sup>	BUS STATE
V <sub>ID</sub> ≥ 0.9 V	L	DOMINANT
0.5 V < V <sub>ID</sub> < 0.9 V	?	?
V <sub>ID</sub> ≤ 0.5 V	Н	RECESSIVE
Open	Н	RECESSIVE

(1) H = high level; L = low level; X = irrelevant; ? = indeterminate; Z = high impedance

#### PARAMETER MEASUREMENT INFORMATION

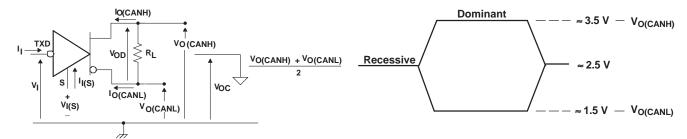


Figure 1. Driver Voltage, Current, and Test Definition

Figure 2. Bus Logic State Voltage Definitions

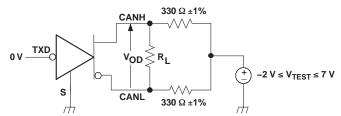


Figure 3. Driver  $V_{\text{OD}}$  Test Circuit



### PARAMETER MEASUREMENT INFORMATION (continued)

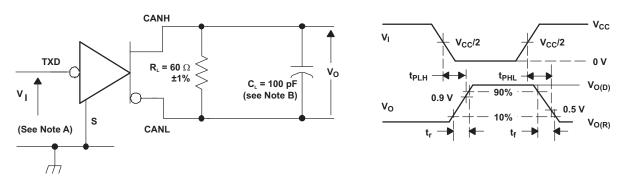


Figure 4. Driver Test Circuit and Voltage Waveforms

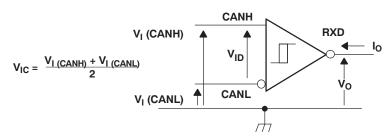
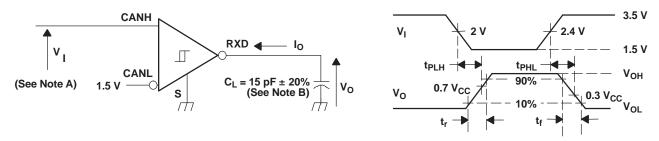


Figure 5. Receiver Voltage and Current Definitions



- A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  125 kHz, 50% duty cycle,  $t_r \leq$  6 ns,  $t_f \leq$  6ns,  $Z_O =$  50  $\Omega$ .
- B. C<sub>L</sub> includes instrumentation and fixture capacitance within 20%.

Figure 6. Receiver Test Circuit and Voltage Waveforms

	INPUT			OUTPUT
V <sub>CANH</sub>	V <sub>CANL</sub>	V <sub>ID</sub>		R
–11.1 V	–12 V	900 mV	L	V <sub>OL</sub>
12 V	11.1 V	900 mV	L	
-6 V	-12 V	6 V	L	
12 V	6 V	6 V	L	
–11.5 V	–12 V	500 mV	Н	V <sub>OH</sub>
12 V	11.5 V	500 mV	Н	
-12 V	-6 V	6 V	Н	
6 V	12 V	6 V	Н	
Open	Open	X	Н	

Table 1. Differential Input Voltage Threshold Test



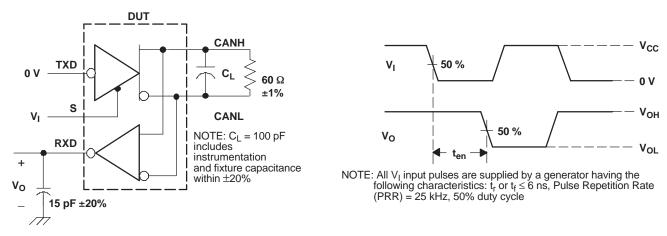
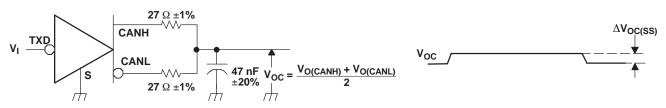
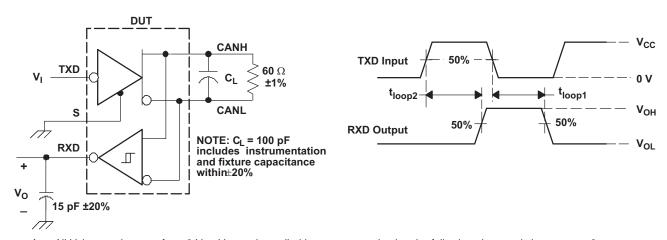


Figure 7. t<sub>en</sub> Test Circuit and Waveform



NOTE: All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

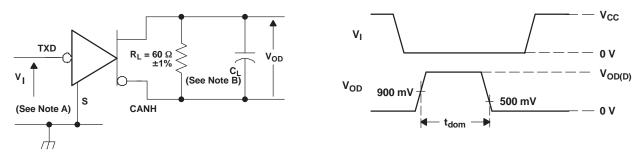
Figure 8. Common Mode Output Voltage Test and Waveforms



A. All  $V_I$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

Figure 9. t<sub>(LOOP)</sub> Test Circuit and Waveform





- A. All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 500 Hz, 50% duty cycle.
- B.  $C_L = 100 \text{ pF}$  includes instrumentation and fixture capacitance within  $\pm 20\%$ .

Figure 10. Dominant Time-Out Test Circuit and Waveforms

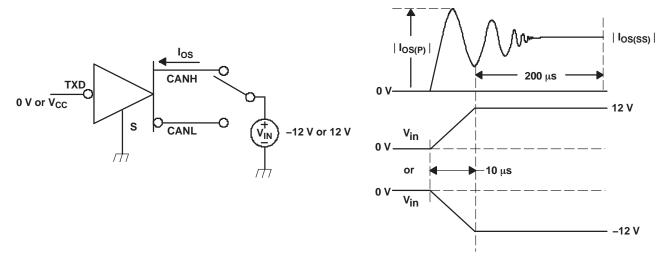


Figure 11. Driver Short-Circuit Current Test and Waveform



#### **DEVICE INFORMATION**

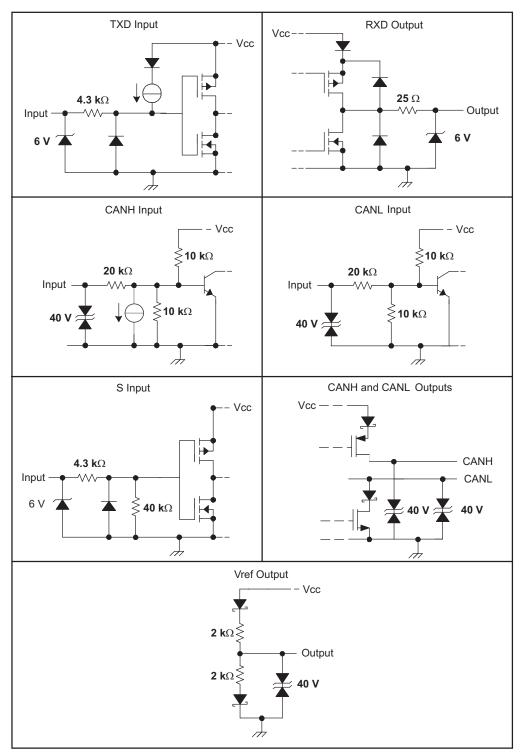
Table 2. Parametric Cross Reference With the TJA1050

PARAMETER	HVD1050						
TRANSMITTER SECTION           VIH         High-level input voltage         Recommended VIH							
High-level input voltage	Recommended V <sub>IH</sub>						
Low-level input voltage	Recommended V <sub>IL</sub>						
High-level input current	Driver I <sub>IH</sub>						
Low-level input current	Driver I <sub>IL</sub>						
BUS SE	CTION						
Power-off bus input current	Receiver I <sub>I(off)</sub>						
Short-circuit output current	Driver I <sub>OS(SS)</sub>						
Dominant output voltage	Driver V <sub>O(D)</sub>						
Differential input voltage	Receiver V <sub>IT</sub> and recommended V <sub>ID</sub>						
Diffrential input hysteresis	Receiver V <sub>hys</sub>						
Recessive output voltage	Driver V <sub>O(R)</sub>						
Differential bus voltage	Driver V <sub>OD(D)</sub> and V <sub>OD(R)</sub>						
CANH, CANL input resistance	Receiver R <sub>IN</sub>						
Differential input resistance	Receiver R <sub>ID</sub>						
Input resistance matching	Receiver R <sub>I (m)</sub>						
Input capacitance to ground	Receiver C <sub>I</sub>						
Differential input capacitance	Receiver C <sub>ID</sub>						
RECEIVER	SECTION						
High-level output current	Recommended I <sub>OH</sub>						
Low-level output current	Recommended I <sub>OL</sub>						
Vref PIN S	SECTION						
Reference output voltage	Vo						
TIMING S	SECTION						
Delay TXD to bus active	Driver t <sub>PLH</sub>						
Delay TXD to bus inactive	Driver t <sub>PHL</sub>						
Delay bus active to RXD	Receiver t <sub>PHL</sub>						
Delay bus inactive to RXD	Receiver t <sub>PLH</sub>						
$t_{d(TXD-BUSon)} + t_{d(BUSon-RXD)}$	Device t <sub>LOOP1</sub>						
$t_{d(TXD-BUSoff)} + t_{d(BUSoff-RXD)}$	Device t <sub>LOOP2</sub>						
Dominant time out	Driver t <sub>(dom)</sub>						
S PIN SI	ECTION						
High-level input voltage	Recommended V <sub>IH</sub>						
Low-level input voltage	Recommended V <sub>IL</sub>						
High-level input current	I <sub>IH</sub>						
Low-level input current	I <sub>IL</sub>						
	High-level input voltage Low-level input voltage High-level input current Low-level input current BUS SE Power-off bus input current Short-circuit output current Dominant output voltage Differential input voltage Differential input hysteresis Recessive output voltage Differential bus voltage CANH, CANL input resistance Differential input resistance Input resistance matching Input capacitance to ground Differential input capacitance  RECEIVER High-level output current Low-level output current Vref PIN S Reference output voltage  Delay TXD to bus active Delay TXD to bus inactive Delay bus active to RXD Delay bus inactive to RXD  td(TXD-BUSoff) + td(BUSoff-RXD) Dominant time out  S PIN SI High-level input voltage High-level input current						

<sup>(1)</sup> From TJA1050 Product Specification, Philips Semiconductors, 2002 May 16.



### **Equivalent Input and Output Schematic Diagrams**





#### TYPICAL CHARACTERISTICS



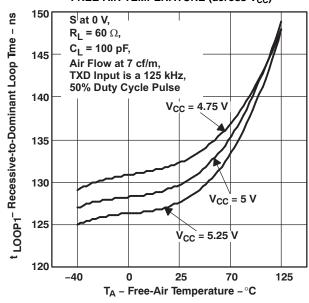


Figure 12.

## DOMINANT-TO-RECESSIVE LOOP TIME VS FREE-AIR TEMPERATURE (across V<sub>CC</sub>)

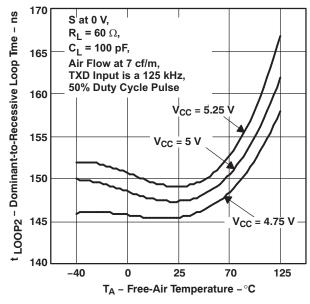


Figure 13.

## SUPPLY CURRENT (RMS) vs SIGNALING RATE

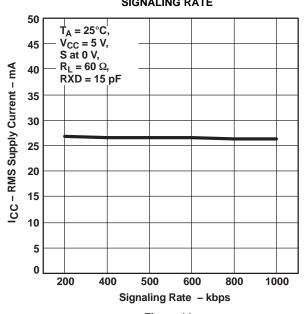


Figure 14.

## DRIVER LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

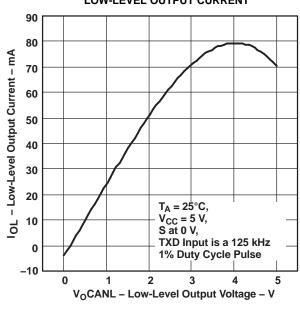


Figure 15.



#### **TYPICAL CHARACTERISTICS (continued)**

### DRIVER HIGH-LEVEL OUTPUT VOLTAGE vs

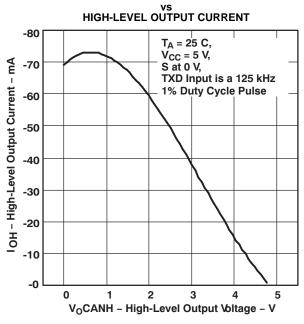


Figure 16.

## DRIVER OUTPUT CURRENT vs SUPPLY VOLTAGE

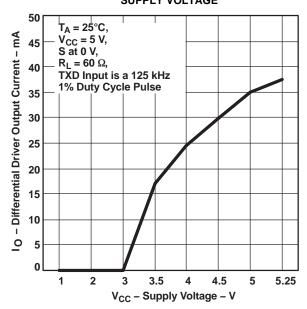


Figure 18.

# DRIVER DIFFERENTIAL OUTPUT VOLTAGE VS FREE-AIR TEMPERATURE (across V<sub>CC</sub>)

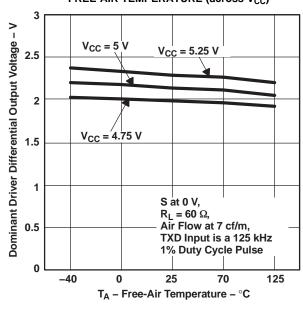


Figure 17.

## RECEIVER OUTPUT VOLTAGE VS DIFFERENTIAL INPUT VOLTAGE

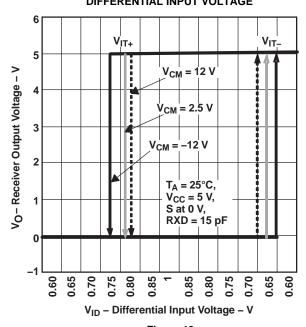


Figure 19.



#### **TYPICAL CHARACTERISTICS (continued)**

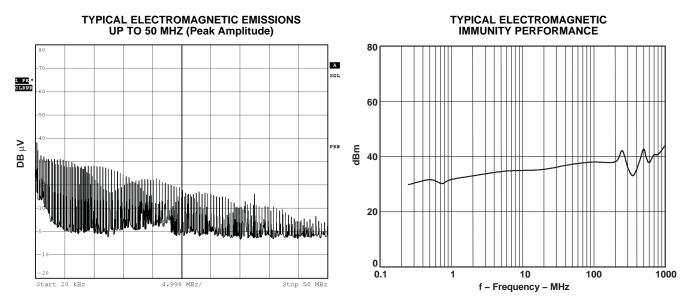


Figure 20. Frequency Spectrum of Common-Mode Emissions

Figure 21. Direct Power Injection (DPI) Response vs Frequency



#### **APPLICATION INFORMATION**

#### THERMAL SHUTDOWN

The SN65HVD1050 has a thermal shutdown feature that turns off the driver outputs when the junction temperature nears 190°C. This shutdown prevents catastrophic failure from bus shorts, but does not protect the circuit from possible damage. The user should strive to maintain recommended operating conditions and not exceed absolute-maximum ratings at all times. If an SN65HVD1050 is subjected to many, or long-duration faults that can put the device into thermal shutdown, it should be replaced.





i.com 26-Apr-2007

#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65HVD1050D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD1050DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD1050DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD1050DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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#### TAPE AND REEL INFORMATION





Α	0	Dimension designed to accommodate the component width
В	0	Dimension designed to accommodate the component length
		Dimension designed to accommodate the component thickness
٧	٧	Overall width of the carrier tape
ГР	1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD1050DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1





#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD1050DR	SOIC	D	8	2500	346.0	346.0	29.0

### D (R-PDSO-G8)

### PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



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